

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	1	high near1 impurity near1 tantalum	USPAT; US-PGPUB; ;EPO; JPO; DERWENT; IBM-TDB	2002/11/07 17:20	
2	BRS	L2	141	high near1 purity near1 tantalum	USPAT; US-PGPUB; ;EPO; JPO; DERWENT; IBM-TDB	2002/11/07 17:20	
3	BRS	L3	12	(high near1 purity near1 tantalum) near15 (weight)	USPAT; US-PGPUB; ;EPO; JPO; DERWENT; IBM-TDB	2002/11/07 17:26	
4	BRS	L4	12	(purity near1 tantalum) near15 (weight)	USPAT; US-PGPUB; ;EPO; JPO; DERWENT; IBM-TDB	2002/11/07 17:27	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
5	BRS	L5	653	(tantalum) near15 (weight) near15 (metal\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2002/11/07 17:28	
6	BRS	L6	4	(tantalum) near15 (weight) near15 (metallic near3 impurities)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2002/11/07 17:31	
7	BRS	L7	85	(tantalum) near15 (weight) near15 (metallic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2002/11/07 17:31	
8	BRS	L10	3	(tantalum) near15 (weight) near15 (metallic) near10 (tungsten or molybdenum) near15 (ppm)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2002/11/07 17:33	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
9	BRS	L8	40	(tantalum) near15 (weight) near15 (metallic) near10 (tungsten or molybdenum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2002/11/07 17:55	
10	BRS	L11	2745	"Ta2O5"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2002/11/07 17:55	
11	BRS	L13	4	"Ta2O5" near10 (weight) near10 (metal\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2002/11/07 17:57	
12	BRS	L14	0	"Ta2O5" near10 (weight) near10 (metallic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2002/11/07 17:57	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L15	0	"Ta205" near10 (weight) near10 (tungsten or molybdenum)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM- TDB	2002/11/07 17:57	
14	BRS	L12	142	"Ta205" near10 (weight)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM- TDB	2002/11/07 18:03	
15	BRS	L16	47	"Ta.sub.20.sub.5" near10 (weight)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM- TDB	2002/11/07 18:03	

	U	1	Document ID	Title	Current OR	Pages	Issue Date
1	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 20020132388 A1	Tantalum sputtering target and method of manufacture	438/77	11	20020919
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6323055 B1	Tantalum sputtering target and method of manufacture	438/77	12	20011127
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6323055 B	Highly pure tantalum preparation method for use in manufacture of electronic capacitors, bulk capacitors, thin film capacitors		12	20020611

	U	1	Document ID	Title	Current OR	Pages	Issue Date
1	<input checked="" type="checkbox"/>	<input type="checkbox"/>	JP 2000165001 A	DIELECTRIC CIRCUIT BOARD		6	20000616
2	<input type="checkbox"/>	<input type="checkbox"/>	US 5188990 A	Low temp. metal oxide glass sealing compsn., for semiconductor packages, etc. - comprise tellurium oxide, vanadium oxide and other metal oxide(s) pref. niobium-, zirconium- and/or zinc-oxide(s)		6	19930223
3	<input checked="" type="checkbox"/>	<input type="checkbox"/>	JP 55060041 A	Infrared spectrum transmitting glass - contains oxides of germanium, aluminium, tantalum, and barium, opt. together with other oxides		3	19800506
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	DE 2844558 A	Stable electrodes, esp. anodes for electrolysis in acid medium - having coating of insol. metal tungstate, tantalum oxide and noble metal oxide		22	19790510